NSN 5961-01-267-2280

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-267-2280 **Inclosure Material:** Metal and plastic **Overall Length:** 16.51 millimeters **Terminal Length:** 14.73 millimeters **Overall Height:** 4.82 millimeters **Overall Width:** 10.66 millimeters **Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-220ab **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 repetitive peak reverse voltage and 600.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 25.00 amperes forward current, total rms horsepower metric and 300.00 amperes peak forward surge current nanoamperes **Power Rating Per Characteristic:** 500.0 milliwatts small-signal input power, common-collector universal and 20.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 129.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 3 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** No